

AMENDMENTS

In the Specification

Please replace the Abstract on pages 26-27 with the following clean replacement Abstract. Applicant respectfully asserts that the following paragraph is in accordance with 37 C.F.R. § 1.72(b).

--Methods of forming thin film transistors, and transistors therefrom, are provided where at least one of the source or drain region is conductively doped while conductivity doping of the channel region is prevented without any masking by any separate masking layer. Methods include, providing a substrate having a conductive node; providing a first dielectric layer, a gate layer over the first layer and a second dielectric layer over the gate layer; providing a contact opening through the first and second layers and the gate layer, the opening defining projecting sidewalls; providing a gate dielectric layer within the opening; providing a layer of semiconductive material over the second layer, against the gate dielectric layer and in electrical communication with the node; the material defining a channel region; and conductively doping the semiconductive material layer lying outwardly of the contact opening to form one of a source region or a drain region.--

A marked up version showing amendments is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(b)(1)(ii).

Respectfully submitted,

Dated:

Sept 5, 2001

By:

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/920,979
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Inventor..... H. Montgomery Manning
Assignee Micron Technology, Inc.
Group Art Unit unknown
Examiner undknow
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Title: Thin Film Transistors and Methods of Forming Thin Film Transistors

VERSION WITH MARKINGS TO SHOW CHANGES MADE
ACCOMPANYING RESPONSE TO AUGUST 29, 2001 NOTICE TO FILE
CORRECTED APPLICATION PAPERS

The Abstract of Disclosure has been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

~~A method~~ Methods of forming a thin film transistors, and transistors therefrom, are ~~over a substrate~~ is provided whereby at least one of the source region or the drain region is conductively doped while preventing conductivity doping of the channel region is prevented without any masking of the channel region occurring by any separate masking layer. ~~A method~~ Methods includes, a) providing a substrate having a conductive node; ~~to which electrical connection is to be made;~~ b) providing a first electrically insulative dielectric layer, ~~over the substrate;~~ c) providing an electrically conductive a gate layer over the first dielectric layer; ~~d) providing~~ and a second electrically insulative dielectric layer over the ~~electrically conductive~~ gate layer; e) providing a contact opening through the first and second dielectric layers, and the ~~electrically conductive~~ gate layer, ~~and the first dielectric layer;~~ the contact opening defining projecting sidewalls; f) providing a gate dielectric layer

within the contact opening laterally inward of the projecting sidewalls; g) providing a layer of semiconductive material over the second dielectric layer, and within the contact opening against the gate dielectric layer and in electrical communication with the node; the semiconductive material within the contact opening defining an elongated and outwardly extending a channel region; and the electrical conductance of which can be modulated by means of the adjacent electrically conductive gate and gate dielectric layers; and h) conductively doping the semiconductive material layer lying outwardly of the contact opening to form one of a source region or a drain region of a thin film transistor. Thin film transistor constructions are also disclosed.